

Process for fabricating a plurality of polycrystalline silicon carbide substrates

Abstract

- 5 The invention relates to a process for fabricating a plurality of polycrystalline silicon carbide substrates (200), said process comprising the following steps:
- forming a multilayer structure by alternating deposition of a plurality of polycrystalline silicon carbide layers (20, 21, 22, 23, 24) and a plurality of separating layers (30, 31, 32, 33) on at least one face of a temporary support substrate (10),
- 10 • detaching each polycrystalline silicon layer (20, 21, 22, 23, 24) from the multilayer structure by removing the temporary substrate (10) and each separating layer (30, 31, 32, 33) to form a respective polycrystalline silicon substrate (200).

Figure for the abstract: Fig. 5